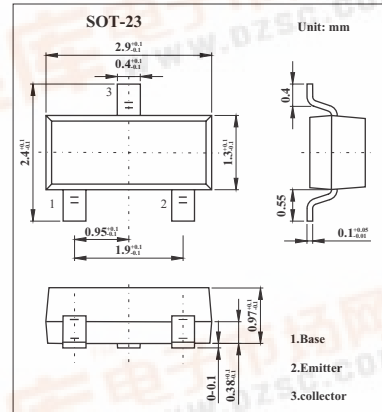


SMD Type Transistors

Silicon NPN Epitaxial Planar Type
2SC2778

■ Features

- Optimum for RF amplification, oscillation, mixing, and IF of FM/AM radios.
- Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	30	V
Collector-emitter voltage	V _{CEO}	20	V
Emitter-base voltage	V _{EBO}	5	V
Collector current	I _c	30	mA
Collector power dissipation	P _c	200	mW
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base voltage	V _{CBO}	I _c = 10μA, I _E = 0	30			V
Collector-emitter voltage	V _{CEO}	I _c = 2 mA, I _B = 0	20			V
Emitter-base voltage	V _{EBO}	I _E = 10μA, I _c = 0	5			V
Forward current transfer ratio	h _{FE}	V _{CE} = 10 V, I _c = 1 mA	70		250	
Transition frequency	f _T	V _{CB} = 10 V, I _E = -1 mA, f = 200 MHz	150	230		MHz
Reverse transfer capacitance	C _{re}	V _{CB} = 10 V, I _E = -1 mA, f = 10.7 MHz		1.3		pF

■ hFE Classification

Marking	KB	KC
h _{FE}	70~160	110~250